

**Amendments to the claims:**

1. (currently amended) A chip for a chip-containing portable article, the chip comprising a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories, and an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon comprising physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength ~~lower~~ longer than 1  $\mu\text{m}$ .
2. (withdrawn) A chip according to Claim 1, wherein the physical means are means providing physical protection against the action of electromagnetic radiation in the infrared range.
3. (withdrawn) A chip according to Claim 2, wherein the physical means are means providing physical protection against the action of electromagnetic radiation in the ultraviolet, visible, and infrared ranges.
4. (cancelled)
5. (previously presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are silicon dopants.
6. (previously presented) A chip according to Claim 5, wherein the concentration of silicon dopants lies in the range  $10^{17}$  to  $10^{20}$  atoms per  $\text{cm}^3$ .
7. (previously presented) A chip according to Claim 5, wherein the silicon dopants are phosphorus or boron.
8. (cancelled)
9. (cancelled)

10. (previously presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by surface irregularities.
11. (cancelled)
12. (previously presented) A chip according to claim 10, wherein the surfaces irregularities are provided in the face of the additional layer of silicon that is in contact with the sealing layer.
13. (previously presented) A chip according to Claim 10, wherein the surface irregularities are provided in the face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.
14. (previously presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by at least one deposition of metal on the additional layer of silicon.
15. (previously presented) A chip according to Claim 14, wherein the metal deposition has a thickness greater than 50 Å.
16. (currently amended) A chip according to Claim 14, wherein the metal deposition is on the face of the additional layer of silicon that is in contact with the sealing layer.
17. (previously presented) A chip according to Claim 14, wherein the metal deposition is on the face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.
18. (cancelled)
19. (previously presented) A chip according to Claim 16, wherein the metal deposition has a thickness of about 100 Å.
20. (previously presented) A portable article provided with a chip that comprises a silicon substrate layer having an active face with circuits integrated therein defining

a central processor unit and memories, the chip further comprising an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon comprising physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1  $\mu\text{m}$ .